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thin solid films

Contents of Volume 321

Preface viii

Conference photo ix

Sponsor x

SiGeC

Si/$Si_{1-x}Ge_x$ and Si/$Si_{1-y}C_y$ heterostructures: materials for high-speed field-effect transistors
F. Schäffler 1

Carbon-containing group IV heterostructures on Si: properties and device applications
H.J. Osten, R. Barth, G. Fischer, B. Heinemann, D. Knoll, G. Lippert, H. Rücker, P. Schley, W. Röpke 11

Optimization of growth conditions for strained Si/$Si_{1-y}C_y$ structures
K.B. Joelsson, W.-X. Ni, G. Pozina, L. Hultman, G.V. Hansson 15

Optimized processing for differentially molecular beam epitaxy-grown SiGe(C) devices
G. Lippert, H.J. Osten, K. Blum, R. Sorge, P. Schley, D. Krüger, G. Fischer 21

Low-temperature molecular beam epitaxy of $Si_{1-x-y}Ge_xC_y$/ Si quantum well structures: electrical and optical properties
D. Grützmacher, R. Hartmann, P. Schnappauf, U. Gennser, E., Müller, D. Bächle, A. Dommann 26

Molecular beam epitaxial growth and photoluminescence investigation of $Si_{1-y}C_y$layers
S. Zerlauth, C. Penn, H. Seyringer, J. Stangl, G. Brunthaler, G. Bauer, F. Schäffler 33

Comparison of Si/$Si_{1-y}Ge_xC_y$ and Si/$Si_{1-y}C_y$ heterojunctions grown by rapid thermal chemical vapor deposition
J.L. Hoyt, T.O. Mitchell, K. Rim, D.V. Singh, J.F. Gibbons 41

Electrical and optical properties of phosphorus doped $Ge_{1-y}C_y$
M.W. Dashiell, R.T. Trooger. K.J. Roe. A-S. Khan, B. Orner. J.O. Olowolafe. P.R. Berger. R.G. Wilson, J. Kolodzey 47

Effective mass measurement in two-dimensional hole gas in strained $Si_{1-x-y}Ge_xC_y$/Si(100) modulation doped heterostructures
C.L. Chang, S.P. Shukla, W. Pan, V. Venkataraman, J.C. Sturm, M. Shayegan 51

SiGe Quantum Dots and Self-Organization

Alignment of Ge three-dimensional islands on faceted Si(001) surfaces
K. Sakamoto, H. Matsuhata, M.O. Tanner, D. Wang, K.L. Wang. 55

Self-organized germanium quantum dots grown by molecular beam epitaxy on Si(100)
Z.-m.Jiang,H.-j.Zhu, F. Lu, J. Qin, D. Huang, X. Wang, C.-w. Hu, Y. Chen, Z. Zhu, T. Yao. 60

Suppression of phonon replica in the radiative recombination of an MBE-grown type-II Ge/Si quantum dot
S. Fukatsu, H. Sunamura, Y. Shiraki, S. Komiyama 65

Influence of pre-grown carbon on the formation of germanium dots
O.G. Schmidt, C. Lange, K. Eberl, O. Kienzle, F. Ernst 70

Direct MBE growth of SiGe dots on ordered mesoporous glass-coated Si substrate
Y.S. Tang, S.J. Cai, G.L. Jin, K.L. Wang, H.M. Soyez, B.S. Dunn. 76

Gas-source molecular beam epitaxial growth of SiGe alloy-based 'naked' quantum wells
Y. Kishimoto, Y. Shiraki, S. Fukatsu. 81

Characterization of self-assembled Ge islands on Si(100) by atomic force microscopy and transmission electron microscopy
G. Wöhl, C. Schöllhorn, O.G. Schmidt, K. Brunner, K., Eberl, O. Kienzle, F. Ernst 86

Bimodal height distribution of self-assembled germanium islands grown on $Si_{0.84}Ge_{0.16}$pseudo-substrates
E.V. Pedersen, F. Jensen, S.Y. Shiryaev, J.W. Petersen, J. Lundsgaard Hansen, A.N. Larsen 92

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Fabrication of SiGe quantum dots: a new approach based on selective growth on chemically prepared H-passivated Si(100) surfaces
V. Le Thanh 98

Quantum wire transistor at locally grown edges
F. Kaesen, W. Hansch, I. Eisele, M. Kalus 106

Growth and Characterization

Growth of SiGe/Si multiple quantum wells by ultra-high-vacuum electron cyclotron resonance chemical vapor deposition
S.-J. Joo, E. Yoon, S.-H. Hwang, K.-W. Whang, S.K. Chun, Y.D. Kim 111

Effect of Sb as a surfactant on the inner diffusion of epilayer Ge atoms into Si substrate
Z. Jiang, A. Xu, D. Hu, H. Zhu, X. Liu, X. Wang, M. Mao, X. Zhang, J. Hu, D. Huang, X. Wang 116

Atomic hydrogen for the formation of abrupt Sb doping profiles in MBE-grown Si
P.E. Thompson, C. Silvestre, M. Twigg, G. Jernigan, D.S. Simons 120

Surfactant-grown low-doped germanium layers on silicon with high electron mobilities
K.R. Hofmann, D. Reinking, M. Kammler, M. Horn-von Hoegen 125

Role of strain in dopant surface segregation during Si and SiGe growth by molecular beam epitaxy
W.-X. Ni, G.V. Hansson, J. Cardenas, B.G. Svensson 131

Artificial substrates for n- and p-type SiGe heterostructure field-effect transistors
T. Hackbarth, H. Kibbel, M. Glueck, G. Hoeck, H.-J. Herzog 136

X-Ray scattering investigation of the interfaces in $Si/Si_{1-x}Ge_x$ superlattices on Si(001) grown by MBE and UHV-CVD
J.-M. Baribeau, H. Lafontaine 141

Quantitative secondary ion mass spectrometry analysis of SiO_2 desorption during in situ heat cleaning
E. Kasper, M. Bauer, M. Oehme 148

Spontaneous oscillator strength modulation in MBE-grown Si/Ge superlattices
Y. Miyake, Y. Shiraki, S. Fukatsu 153

Photoluminescence in UHV-CVD-grown $Si_{1-x}Ge_x$ quantum wells on Si(100): band alignment variation with exctiation density and applied uniaxial stress
N.L. Rowell, G. C. Aers, H. Lafontaine, R.L. Williams 158

Effect of layer thickness variation on light scattering by acoustic phonons in SiGe/Si superlattices
X. Liu, D. Huang, X. Wang, H. Zhu, X. Wang 163

Structural characterization of a UHV/CVD-grown SiGe HBT with graded base
M. Dion, D.C. Houghton, N.L. Rowell, D.D. Perovic, G.C. Aers, S.J. Rolfe, G.I. Sproule, J.R. Phillips 167

Electronic and Photonic Devices

Silicon germanium heterostructures in electronics: the present and the future
D.J. Paul 172

Electrical properties of two-dimensional electron gases grown on cleaned SiGe virtual substrates
D.J. Paul, A. Ahmed, N. Griffin, M. Pepper, A.C. Churchill, D.J. Robbins, D.J. Wallis 181

Near and mid infrared silicon/germanium based photodetection
H. Presting 186

Formation of thin gate oxides on SiGe with atomic oxygen
E.A. Ogryzlo, L. Zheng, B. Heinrich, K. Myrtle, H. Lafontaine 196

Bistable diodes grown by silicon molecular beam epitaxy
X. Zhu, X. Zheng, M. Pak, M.O. Tanner, K.L. Wang 201

Electric field tailoring in MBE-grown vertical sub-100 nm MOSFETs
W. Hansch, V.R. Rao, C. Fink, F. Kaesen, I. Eisele 206

Quantum confined Stark shifts in type-I SiGe quantum structures
J.Y. Kim 215

Luminescence from erbium- and oxygen-doped SiGe grown by molecular beam epitaxy
E. Neufeld, A. Sticht, K. Brunner, G. Abstreiter, H. Bay, Ch. Buchal, H. Holzbrecher 219

Incorporation and luminescence properties of $Er_2O_3$and ErF_3doped Si layers grown by molecular beam epitaxy
W.-X. Ni, K.B. Joelsson, C.-X. Du, G. Pozina, I.A. Buyanova, W.M. Chena, G.V. Hansson, B. Monemar 223

Application of selective epitaxial growth in MBE for short-duration gating systems
V.A. Cers, E.A. Ballik 228

Novel Materials and Methods

Epitaxial Si/SiO_2 low dimensional structures
Y. Ishikawa, N. Shibata, S. Fukatsu 234

Characterization of SiGe strained heterostructures grown by molecular beam epitaxy using a Si effusion cell
H. Yaguchi, T. Yamamoto, Y. Shiraki 241

Molecular beam epitaxy growth and thermal stability of $Si_{1-x}Ge_x$ layers on extremely thin silicon-on insulator substrates
K. Brunner, H. Dobler, G. Abstreiter, H. Schäfer, B. Lustig 245

Self-ordering of $CoSi_2$ precipitates and epitaxial layer growth of $CoSi_2$ on Si(100)
S. Mantl, M. Hacke, H.L. Bay, L. Kappius, S. Mesters 251

Si selective enitaxial growth using Cl_2 nursed molecular flow method
T. Aoyama, S. Saito, T. Tatsumi 256

Low temperature electrical surface passivation of MBE-grown pin diodes by hydrogen and oxygen plasma processes
A. Strass, W. Hansch, F. Kaesen, G. Fehlauer, P. Bieringer, A. Fischer, I. Eisele 261

Author Index of Volume 321 265

Subject Index of Volume 321 267

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